

1N5153 (SILICON)



CASE 47

Silicon high-frequency step-recovery power varactor, designed for high-power, high-frequency harmonic generation applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	75	Vdc
Forward Current	I_F	0.25	Adc
RF Power Input	P_{in}	15	Watts
Total Device Dissipation @ $T_C = 75^\circ\text{C}$ Derate above 75°C	P_D	5.5 45	Watts mW/ $^\circ\text{C}$
Junction Temperature	T_J	+200	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Condition	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$I_R = 10 \mu\text{Adc}$	BV_R	75	80	—	Vdc
Reverse Current	$V_R = 60 \text{ Vdc}$ $V_R = 60 \text{ Vdc}, T_A = 150^\circ\text{C}$	I_R	— —	0.5 —	1.0 100	μAdc
Series Resistance	$V_R = 6 \text{ Vdc}, f = 50 \text{ MHz}$	R_S	—	0.5	—	Ohms
Diode Capacitance	$V_R = 6 \text{ Vdc}, f = 1.0 \text{ MHz}$ $V_R = 70 \text{ Vdc}, f = 1.0 \text{ MHz}$	C_T^*	5.0 —	5.8 4.0	7.5 —	pF
Figure of Merit	$V_R = 6 \text{ Vdc}, f = 50 \text{ MHz}$	Q	—	1100	—	—
Power Output	DOUBLER TEST CIRCUIT (Figure 1) $P_{in} = 12 \text{ W}, f_{in} = 1 \text{ GHz}$ $f_{out} = 2 \text{ GHz}$	P_{out}	6.0	7.2	—	Watts
Efficiency		η	50	60	—	%
Thermal Resistance		θ_J	—	19	23	$^\circ\text{C/Watt}$

$$*C_T = C_J + C_C$$

FIGURE 1 — HARMONIC DOUBLER EFFICIENCY TEST CIRCUIT

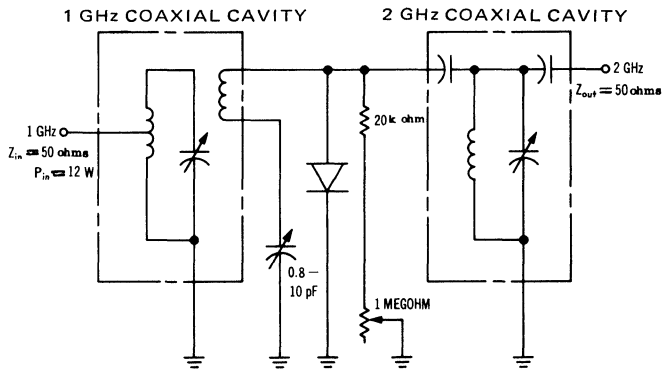
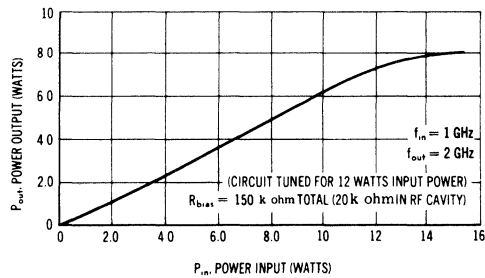


FIGURE 2 — LINEARITY CHARACTERISTIC WITHOUT RETUNING



POWER OUTPUT
versus OUTPUT FREQUENCY
FIGURE 3A — DOUBLING (X2)

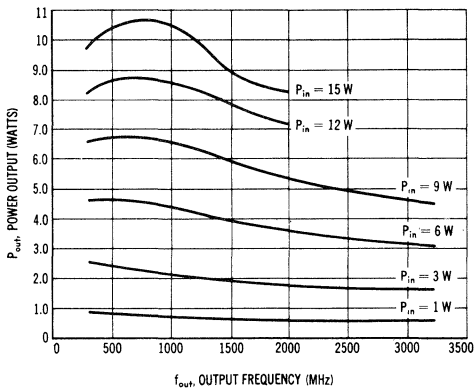


FIGURE 3B — TRIPLING (X3)

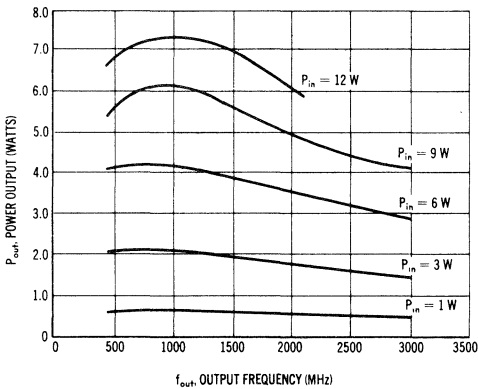
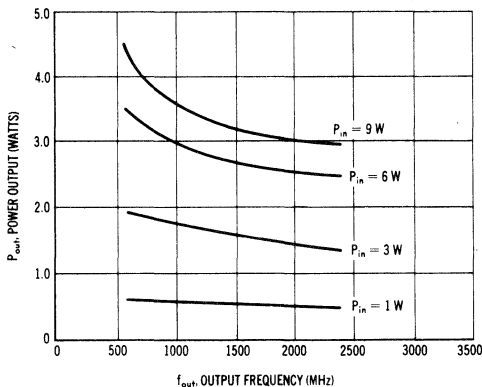


FIGURE 3C — QUADRUPLING (X4)



TYPICAL CHARACTERISTICS at 25°C

FIGURE 4 — FIGURE OF MERIT
versus REVERSE VOLTAGE

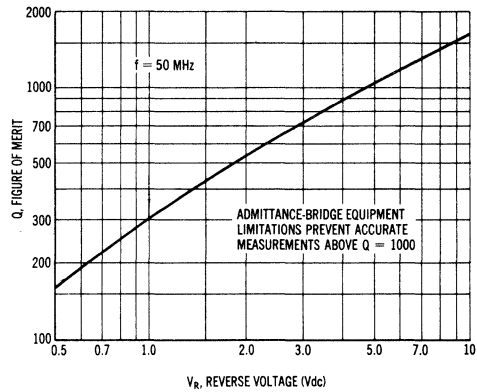


FIGURE 5 — VARACTOR CAPACITANCE
versus REVERSE VOLTAGE

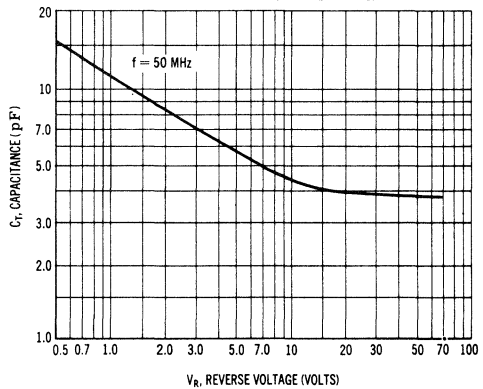


FIGURE 6 — DOUBLER EFFICIENCY
versus CASE TEMPERATURE

